

TOSHIBA**2SC2551**

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC2551

Hight Voltage Control Applications

Plasma Display, Nixie Tube Driver Applications

Cathode Ray Tube Brightness Control Applications

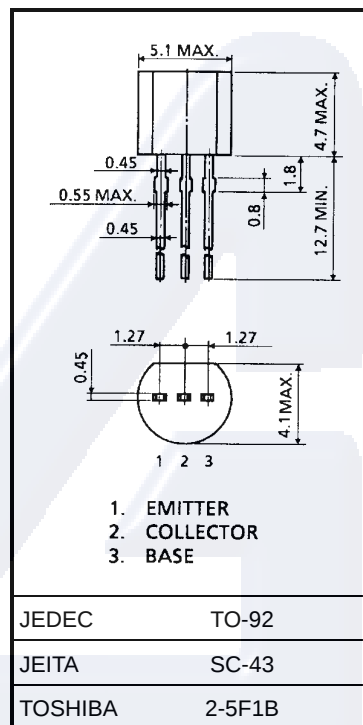
Industrial Applications

Unit: mm

- High voltage: $V_{CBO} = 300\text{ V}$, $V_{CEO} = 300\text{ V}$
- Low saturation voltage: $V_{CE(sat)} = 0.5\text{ V (max)}$
- Small collector output capacitance: $C_{ob} = 3\text{ pF (typ.)}$
- Complementary to 2SA1091.

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	300	V
Collector-emitter voltage	V_{CEO}	300	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	100	mA
Base current	I_B	20	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

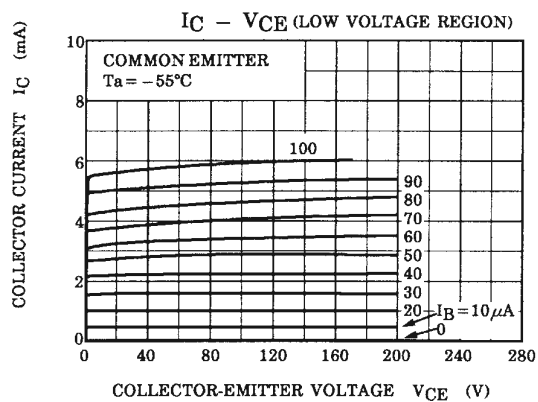
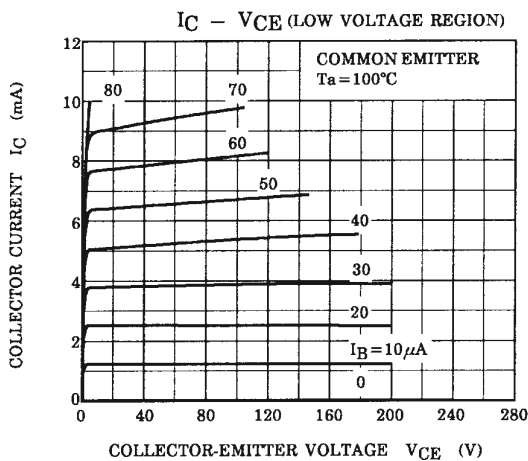
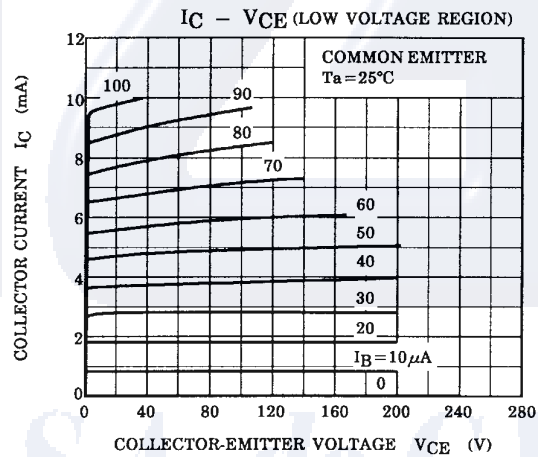
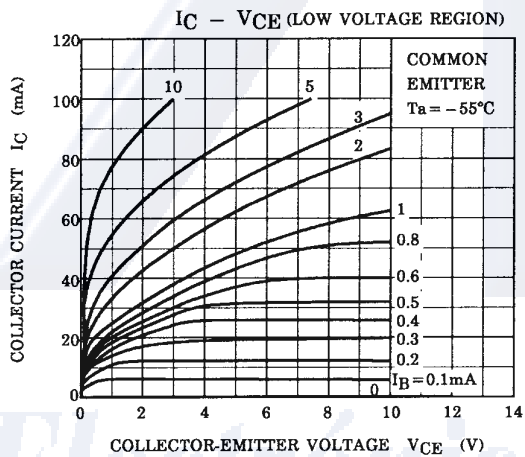
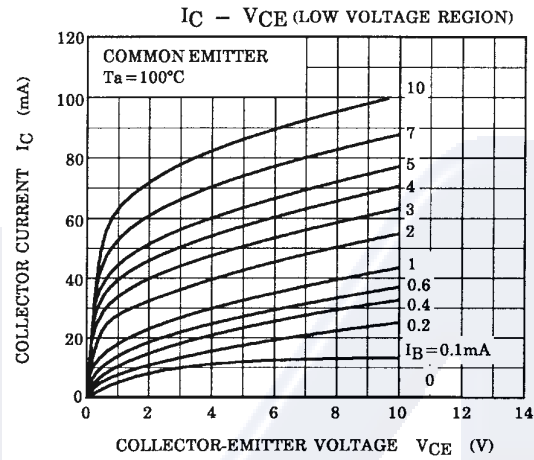
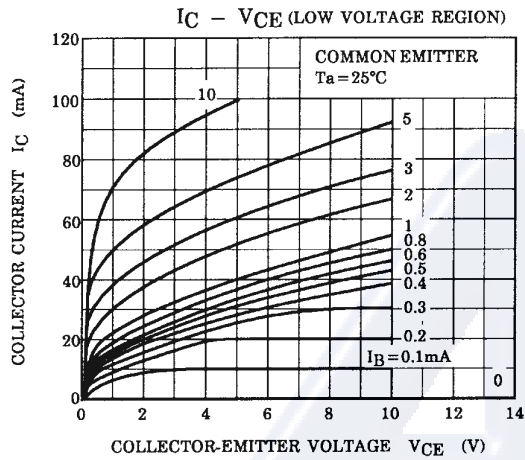


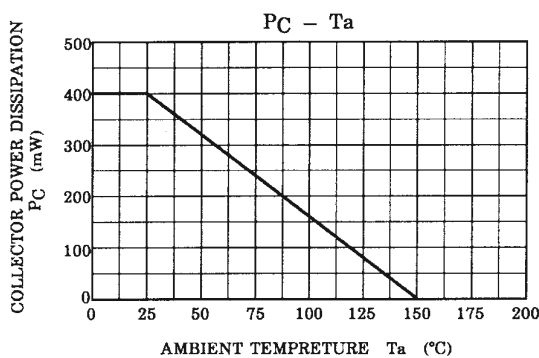
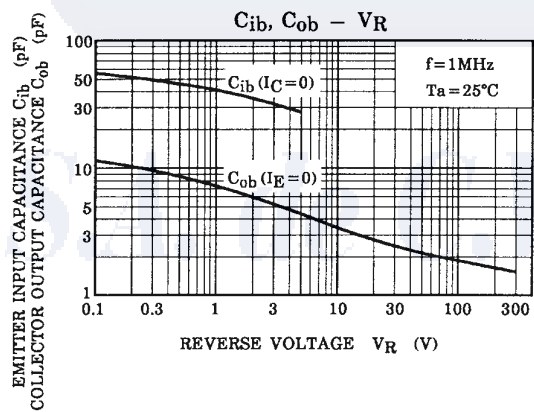
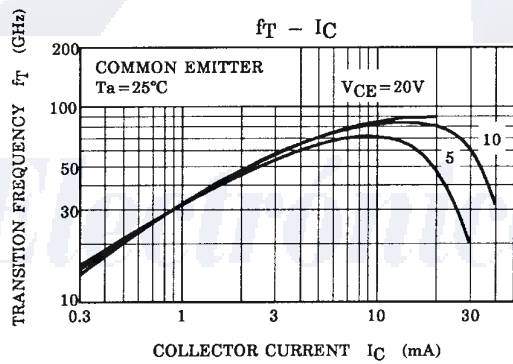
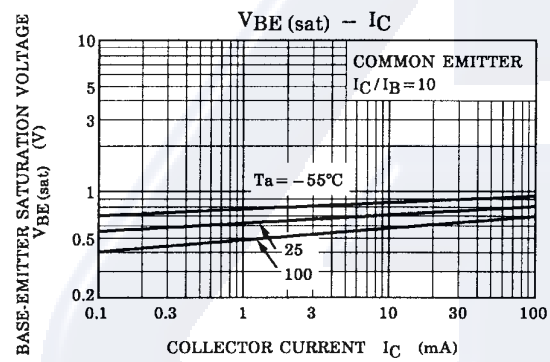
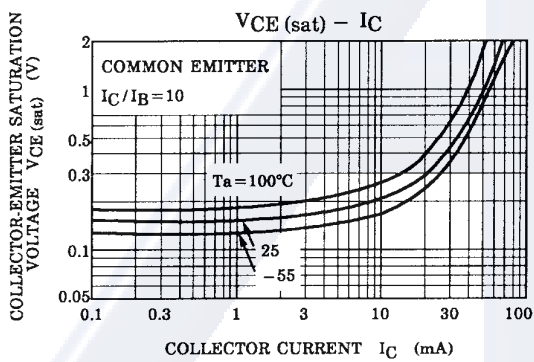
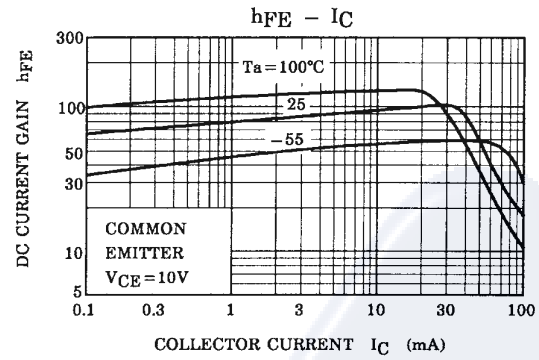
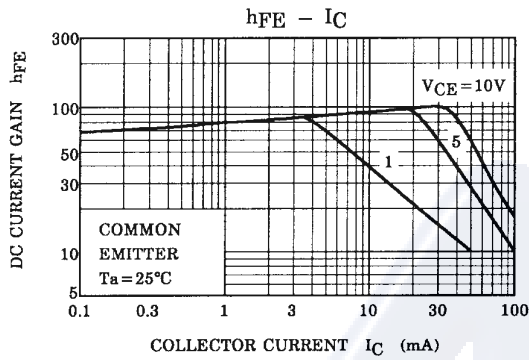
Weight: 0.21 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 300\text{ V}$, $I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 6\text{ V}$, $I_C = 0$	—	—	0.1	μA
Collector-base breakdown voltage	$V_{(BR) CBO}$	$I_C = 0.1\text{ mA}$, $I_E = 0$	300	—	—	V
Collector-emitter breakdown voltage	$V_{(BR) CEO}$	$I_C = 1\text{ mA}$, $I_B = 0$	300	—	—	V
DC current gain	$h_{FE(1)}$ (Note)	$V_{CE} = 10\text{ V}$, $I_C = 20\text{ mA}$	30	—	150	
	$h_{FE(2)}$	$V_{CE} = 10\text{ V}$, $I_C = 1\text{ mA}$	20	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20\text{ mA}$, $I_B = 2\text{ mA}$	—	—	0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 20\text{ mA}$, $I_B = 2\text{ mA}$	50	—	1.2	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}$, $I_C = 20\text{ mA}$	—	80	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 20\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	—	3	4	pF

Note: $h_{FE(1)}$ classification R: 30~90, O: 50~150





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